

D The transistor, fundamental component of integrated circuits

The first transistor was made in germanium by John Bardeen and Walter H. Brattain, in December 1947. The year after, along with William B. Shockley at Bell Laboratories, they developed the bipolar transistor and the associated theory. During the 1950s, transistors were made with silicon (Si), which to this day remains the most widely-used semiconductor due to the exceptional quality of the interface created by silicon and silicon oxide

(SiO₂), which serves as an insulator. In 1958, Jack Kilby invented the **integrated circuit** by manufacturing 5 components on the same **substrate**. The 1970s saw the advent of the first microprocessor, produced by Intel and incorporating 2,250 transistors, and the first memory. The complexity of integrated circuits has grown exponentially (doubling every 2 to 3 years according to “Moore’s law”) as transistors continue to become increasingly miniaturized.

The transistor, a name derived from *transfer* and *resistor*, is a fundamental component of microelectronic integrated circuits, and is set to remain so with the necessary changes at the nanoelectronics scale: also well-suited to amplification, among other functions, it performs one essential basic function which is to open or close a current as required, like a switching device (Figure). Its basic working principle therefore applies directly to processing binary code (0, the current is blocked, 1 it goes through) in logic circuits (inverters, gates, adders, and memory cells).

The transistor, which is based on the transport of **electrons** in a solid and not in a vacuum, as in the electron tubes of the old **triodes**, comprises three **electrodes** (*anode*, *cathode* and *gate*), two of which serve as an electron *reservoir*: the **source**, which acts as the emitter filament of an electron tube, the **drain**, which acts as the collector plate, with the gate as “controller”. These elements work differently in the two main types of transistor used today: *bipolar junction transistors*, which came first, and *field effect transistors (FET)*.

Bipolar transistors use two types of **charge carriers**, electrons (negative charge) and **holes** (positive charge), and are comprised of identically **doped** (p or n) semiconductor substrate parts

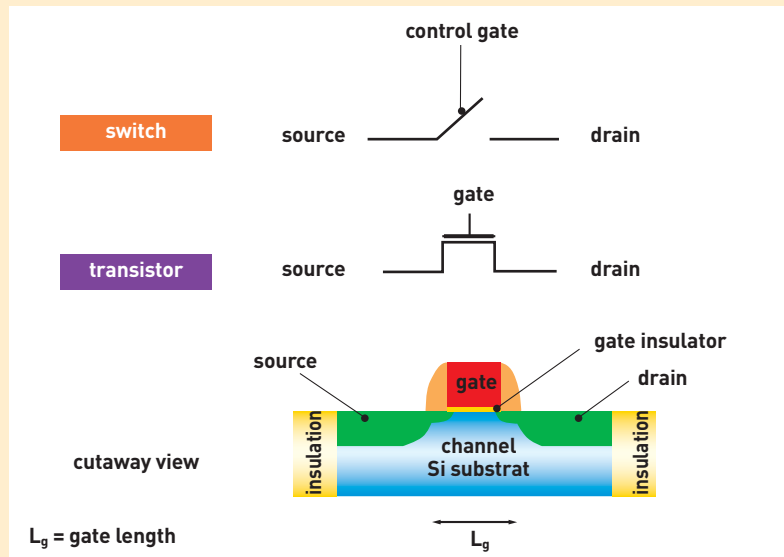


Figure. A MOS transistor is a switching device for controlling the passage of an electric current from the source (S) to the drain (D) via a gate (G) that is electrically insulated from the conducting channel. The silicon substrate is marked B for Bulk.

D (next)

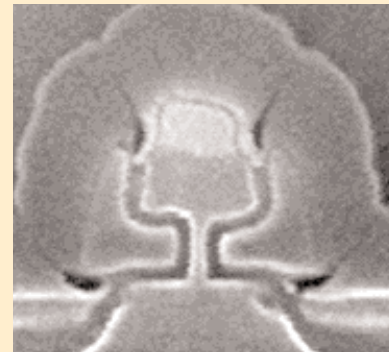
separated by a thin layer of inversely-doped semiconductor. By assembling two semiconductors of opposite types (a p-n junction), the current can be made to pass through in only one direction. Bipolar transistors, whether n-p-n type or p-n-p type, are all basically current amplifier controlled by a gate current⁽¹⁾: thus, in an n-p-n transistor, the voltage applied to the p part controls the flow of current between the two n regions. Logic circuits that use bipolar transistors, which are called TTL (for transistor-transistor logic), consume more energy than field effect transistors which present a zero gate current in off-state and are voltage-controlled.

Field effect transistors, most commonly of MOS (metal oxide semiconductor) type, are used in the majority of today's CMOS (C for complementary) logic circuits⁽²⁾. Two n-type regions are created on a p-type silicon crystal by doping the surface. These two regions, also called drain and source, are thus separated by a very narrow p-type space called the **channel**. The effect of a positive current on the control electrode, naturally called the **gate**, positioned over the semiconductor forces the holes to

the surface, where they attract the few mobile electrons of the semiconductor. This forms a conducting channel between source and drain (Figure). When a negative voltage is applied to the gate, which is electrically insulated by an oxide layer, the electrons are forced out of the channel. As the positive voltage increases, the channel resistance decreases, letting progressively more current through. In an integrated circuit, transistors together with the other components (diodes, condensers, resistances) are initially incorporated into a "chip" with more or less complex functions. The circuit is built by "sandwiching" layer upon layer of conducting materials and insulators formed by **lithography** (Box E, *Lithography, the key to miniaturization*). By far the most classic application of this is the microprocessor at the heart of our computers, which contains several hundred million transistors (whose size has been reduced 10,000-fold since the 1960s), soon a billion. This has led to industrial manufacturers splitting the core of the processors into several subunits working in parallel!



The very first transistor.



8 nanometre transistor developed by the Crolles2 Alliance bringing together STMicroelectronics, Philips and Freescale Semiconductor.

(1) This category includes **Schottky transistors** or **Schottky barrier transistors** which are field effect transistors with a metal/semiconductor control gate that, while more complex, gives improved charge-carrier mobility and response times.

(2) Giving **MOSFET** transistor (for Metal Oxide Semiconductor Field Effect Transistor).

E Lithography, the key to miniaturization

Optical lithography (photolithography) is a major application in the particle-matter interaction, and constitutes the classical process for fabricating **integrated circuits**. It is a key step in defining circuit patterns, and remains a barrier to any future development. Since resolution, at the outset, appears to be directly proportional to wavelength, feature-size first progressed by a step-wise shortening of the wavelength λ of the radiation used.

The operation works via a reduction lens system, by the *exposure* of a photoresist film to energy particles, from the **ultraviolet (UV) photons** currently used through to **X photons, ions**, and finally **electrons**, all through a mask template carrying a pattern of the desired circuit. The aim of all this is to transfer this pattern onto a stack of insulating or conducting layers that make up the mask. These layers will have been deposited previously (the *layering* stage) on a wafer of **semiconductor** material, generally **silicon**. After this process, the resin dissolves under exposure to the air (*development*). The exposed parts of the initial layer can then be etched selectively, then the resin is lifted away chemically before deposition of the following layer. This lithography step can take place over twenty times during the fabrication of an integrated circuit (figure).

In the 1980s, the microelectronics industry used mercury lamps delivering near-UV (g, h and i lines) through quartz optics, with an emission line of 436 **nanometres** (nm). This system was able to etch structures to a feature-size of 3 microns (μm). This system was used through to the mid-90s, when it was replaced by **excimer lasers** emitting far-UV light (KrF, krypton fluoride at 248 nm, then ArF, argon fluoride at 193 nm, with the photons thus created generating several **electronvolts**) that were able to reach a resolution of 110 nm, pushed to under 90 nm with new processes.

In the 1980s, the CEA's Electronics and Information Technology Laboratory (Leti) pioneered the application of lasers in lithography and the fabrication of integrated circuits using excimer lasers, and even the most advanced integrated circuit production still uses these sources.



Photolithography section in ultra-clean facilities at the STMicroelectronics unit in Crolles (Isère).

The next step for high-volume production was expected to be the F_2 laser ($\lambda = 157 \text{ nm}$), but this lithography technology has to all intents and purposes been abandoned due to complications involved in producing optics in CaF_2 , which is transparent at this wavelength. While the shortening of wavelengths in exposure tools has been the driving factor behind the strong resolution gain already achieved, two other factors have nevertheless played key roles. The first was the development of **polymer-lattice photoresists** with low absorbance at the wavelengths used, implementing progressively more innovative input energy reflection/emission systems. The second was enhanced optics reducing diffraction interference (better surface

quality, increase in **numerical aperture**).

Over the years, the increasing complexity of the optical systems has led to resolutions actually *below* the source wavelength. This development could not continue without a major technological breakthrough, a huge step forward in wavelength. For generations of integrated circuits with a lowest resolution of between 80 and 50 nm (the next "node" being at 65 nm), various different approaches are competing to offer particle projection at ever-shorter wavelengths. They use

either "soft" **X-rays** at extreme ultraviolet wavelength (around 10 nm), "hard" X-rays at wavelengths below 1 nm, ions or electrons.

The step crossing below the 50 nm barrier will lead towards low-electron-energy (10 eV)-enabled nanolithography with technology solutions such as the scanning **tunnelling microscope** and **molecular beam epitaxy** (Box C) for producing "superlattices".

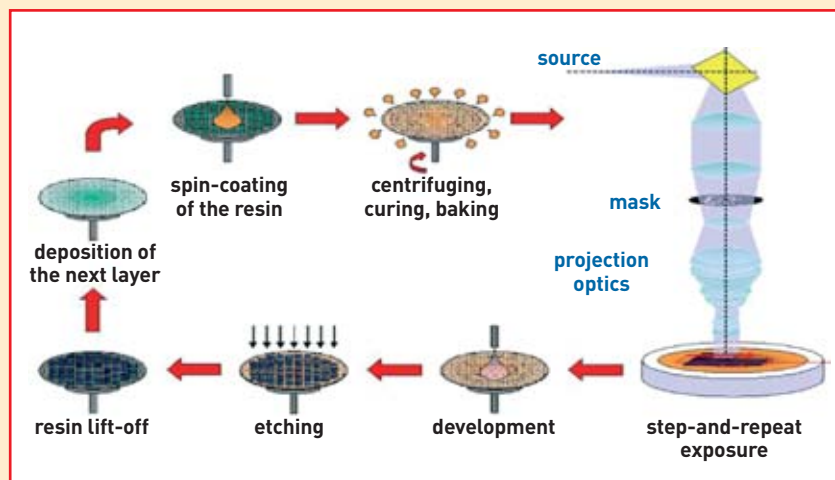


Figure. The various phases in the lithography process are designed to carve features out of the layers of conducting or insulating materials making up an integrated circuit. The sequences of the operation are laying of a photoresist, then projecting the pattern on a mask using a reduction optics system, which is followed by dissolution of the resin that is exposed to the light beam (development). The exposed parts of the initial layer can then be etched selectively, then the resin is lifted away before deposition of the following layer.